



**THE DATASHEET OF
W24257S-70LL**



W24257

32K × 8 CMOS STATIC RAM

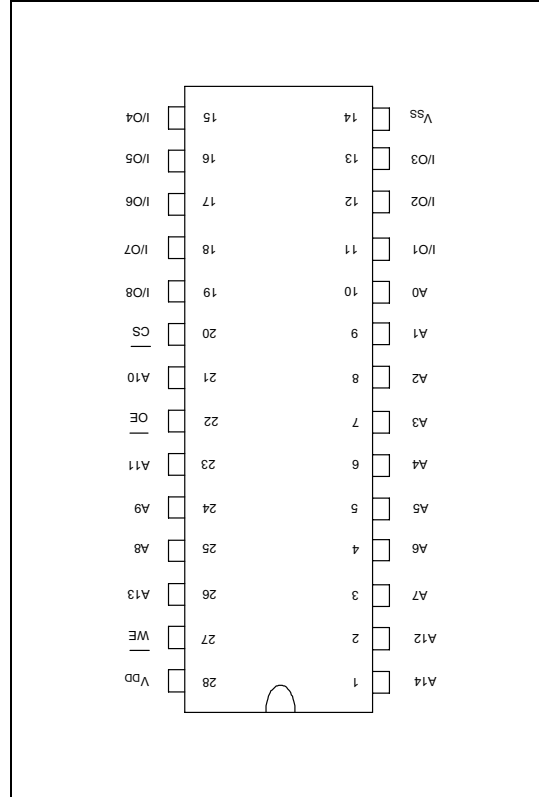
GENERAL DESCRIPTION

The W24257 is a slow speed, low power CMOS static RAM organized as 32768 × 8 bits that operates on a single 5-volt power supply. This device is manufactured using Winbond's high performance CMOS technology.

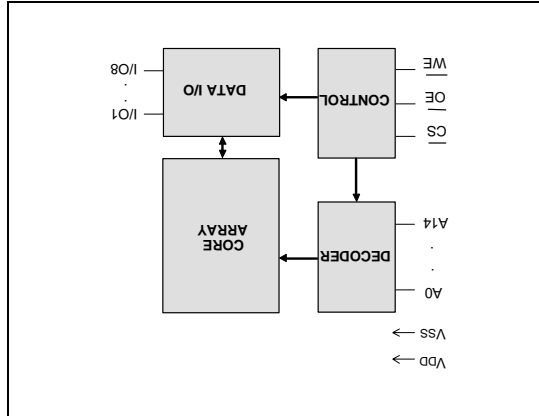
FEATURES

- Low power consumption:
 - Active: 325 mW (max.)
 - Standby: 75 μ W (max.) (LL-version)
 - 150 μ W (max.) (L-version)
- Access time: 70 ns (max.)
- Single +5V power supply
- Fully static operation
- All inputs and outputs directly TTL compatible
- Three-state outputs
- Battery back-up operation capability
- Data retention voltage: 2V (min.)
- Packaged in 28-pin 330 mil SOP, standard type one TSOP (8 mm x 13.4 mm)

PIN CONFIGURATION



BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0-A14	Address Inputs
I/O1-I/O8	Data Inputs/Outputs
CS	Chip Select Input
WE	Write Enable Input
OE	Output Enable Input
VDD	Power Supply
VSS	Ground



Note: Typical characteristics are at VDD = 5V, TA = 25°C.

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Input Low Voltage	VIL	-	-0.5	-	+0.8	V	
Input High Voltage	VIH	-	+2.2	-	VDD+0.5	V	
Input Leakage Current	ILI	VIN = VSS to VDD	-2	-	+2	µA	
Output Leakage Current	ILO	VIO = VSS to VDD, CS = VIH (min.) or OE = VIH (min.) or WE = VIL (max.)	-2	-	+2	µA	
Output Low Voltage	VOL	IOL = +4.0 mA	-	-	0.4	V	
Output High Voltage	VOH	IOH = -1.0 mA	2.4	-	-	V	
Operating Power Supply Current	IDD	CS = VIL (min.), I/O = 0 mA Cycle = min., Duty = 100%	-	-	65	mA	
Standby Power Supply Current	ISB	CS = VIH (min.) Cycle = min., Duty = 100%	-	-	3	mA	
	ISB1	CS ≥ VDD-0.2V	LL	-	-	15	µA
			L	-	-	30	µA

(VDD = 5V ±10%, VSS = 0V, TA = 0 to 70°C)

Operating Characteristics

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

PARAMETER	RATING	UNIT
Supply Voltage to VSS Potential	-0.5 to +7.0	V
Input/Output to VSS Potential	-0.5 to VDD+0.5	V
Allowable Power Dissipation	1.0	W
Storage Temperature	-65 to +150	°C
Operating Temperature	0 to +70	°C

Absolute Maximum Ratings

DC CHARACTERISTICS

CS	OE	WE	MODE	I/O1-I/O8	VDD CURRENT
H	X	X	Not Selected	High Z	ISB, ISB1
L	H	H	Output Disable	High Z	IDD
L	L	H	Read	Data Out	IDD
L	X	L	Write	Data In	IDD

TRUTH TABLE



W24257

CAPACITANCE

(V_{DD} = 5V, T_A = 25°C, f = 1 MHz)

PARAMETER	SYM.	CONDITIONS	MAX.	UNIT
Input Capacitance	C _{IN}	V _{IN} = 0V	6	pF
Input/Output Capacitance	C _{I/O}	V _{OUT} = 0V	8	pF

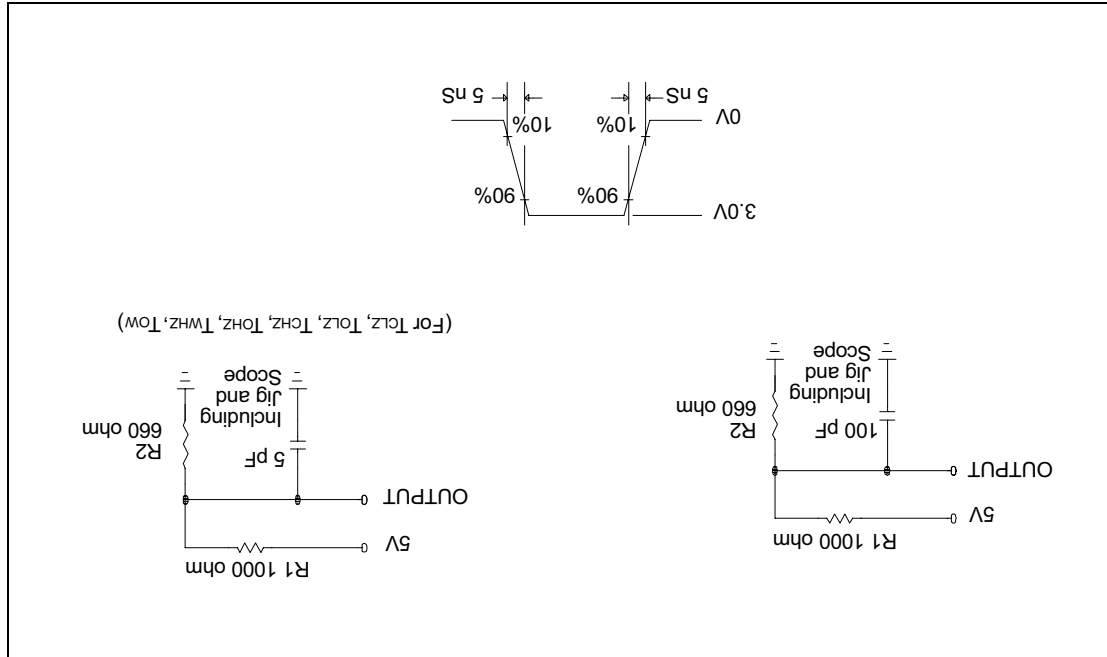
Note: These parameters are sampled but not 100% tested.

AC CHARACTERISTICS

AC Test Conditions

PARAMETER	CONDITIONS
Input Pulse Levels	0.6V to 2.4V
Input Rise and Fall Times	5 nS
Input and Output Timing Reference Level	1.5V
Output Load	CL = 100 pF, I _{OH/IOL} = -1 mA/4 mA

AC Test Loads and Waveform



AC Characteristics, continued

(V_{DD} = 5V ±10%, V_{SS} = 0V, T_A = 0 to 70°C)

Read Cycle

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
		W24257-70		
Read Cycle Time	TRC	70	-	ns
Address Access Time	TAA	-	70	ns
Chip Select Access Time	TACS	-	70	ns
Output Enable to Output Valid	TAOE	-	35	ns
Chip Selection to Output in Low Z	TCLZ*	10	-	ns
Output Enable to Output in Low Z	TOLZ*	5	-	ns
Chip Deselection to Output in High Z	TCHZ*	-	30	ns
Output Disable to Output in High Z	TOHZ*	-	30	ns
Output Hold from Address Change	TOH	10	-	ns

* These parameters are sampled but not 100% tested

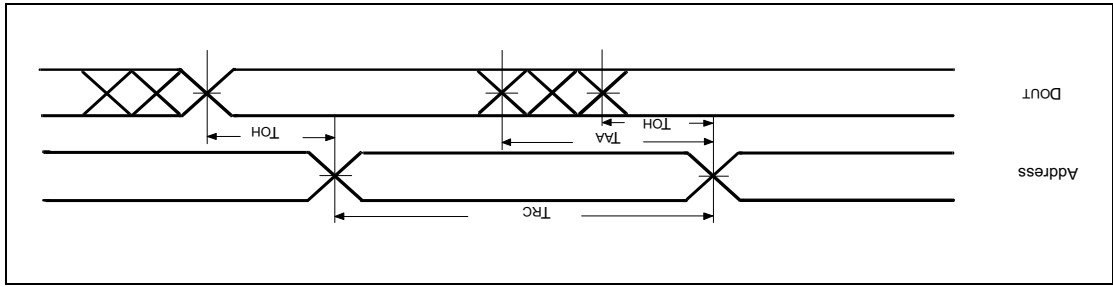
Write Cycle

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
		W24257-70		
Write Cycle Time	TWC	70	-	ns
Chip Selection to End of Write	TCW	60	-	ns
Address Valid to End of Write	TAW	60	-	ns
Address Setup Time	TAS	0	-	ns
Write Pulse Width	TWP	45	-	ns
Write Recovery Time	TWR	0	-	ns
Data Valid to End of Write	TDW	30	-	ns
Data Hold from End of Write	TDH	0	-	ns
Write to Output in High Z	TWHZ*	-	30	ns
Output Disable to Output in High Z	TOHZ*	-	30	ns
Output Active from End of Write	TOW	0	-	ns

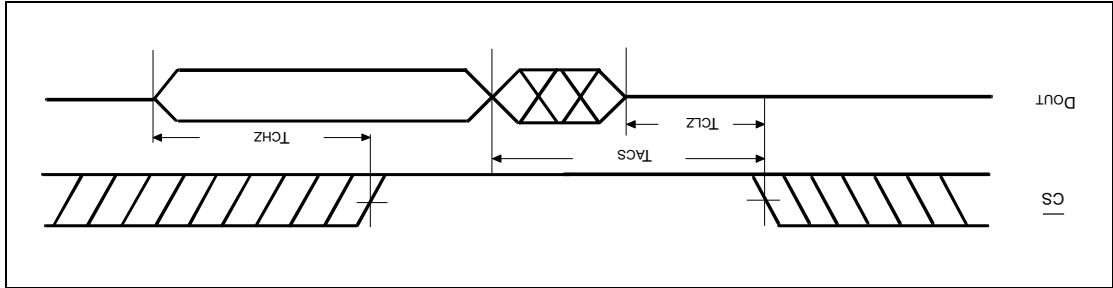
* These parameters are sampled but not 100% tested

TIMING WAVEFORMS

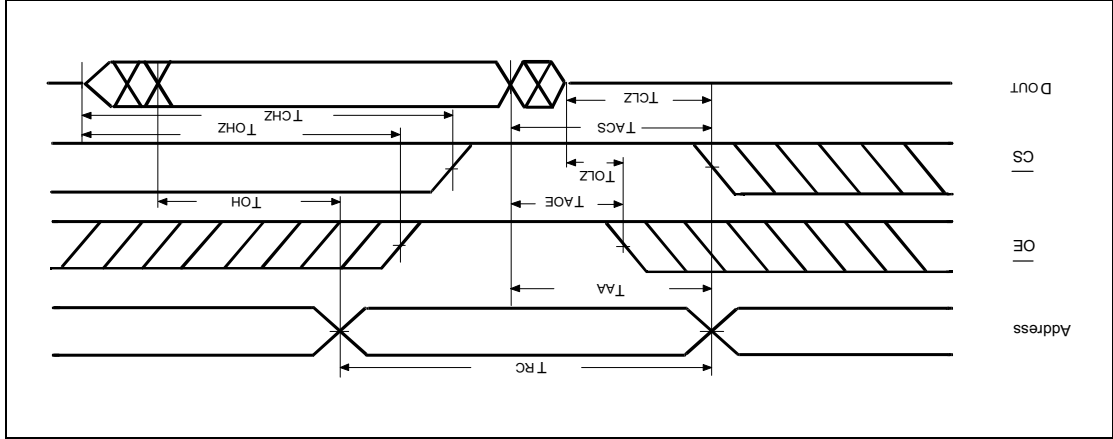
Read Cycle 1 (Address Controlled)



Read Cycle 2 (Chip Select Controlled)

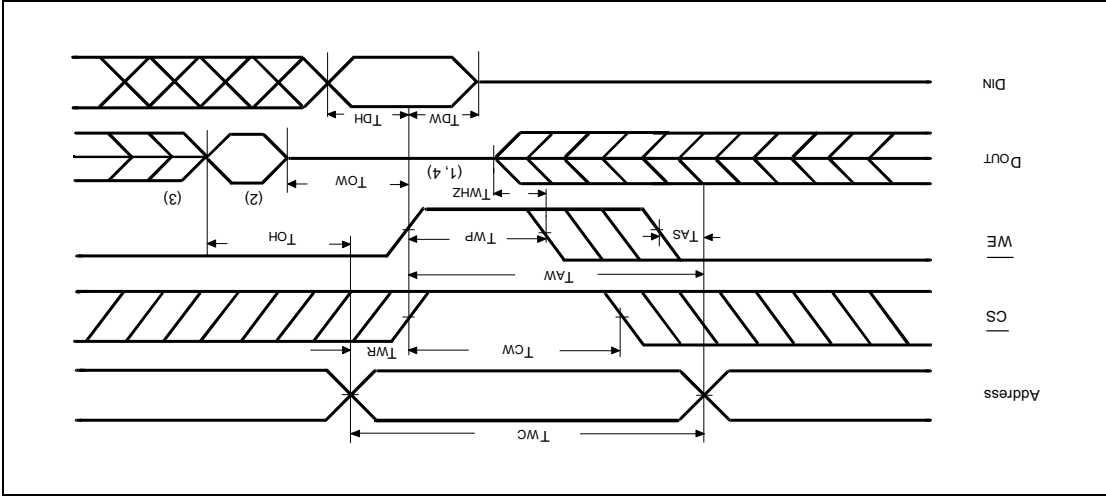


Read Cycle 3 (Output Enable Controlled)

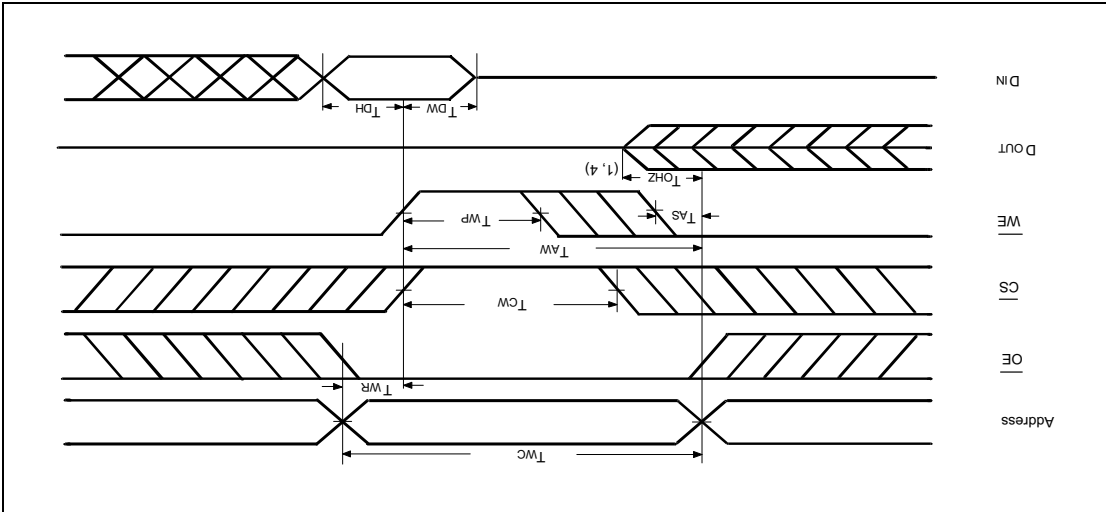


1. During this period, I/O pins are in the output state, so input signals of opposite phase to the outputs should not be applied.
2. The data output from DOUT are the same as the data written to DIN during the write cycle.
3. DOUT provides the read data for the next address.
4. Transition is measured ± 500 mV from steady state with $C_L = 5$ pF. This parameter is guaranteed but not 100% tested.

Notes:



Write Cycle 2
(OE = VIL Fixed)



Write Cycle 1

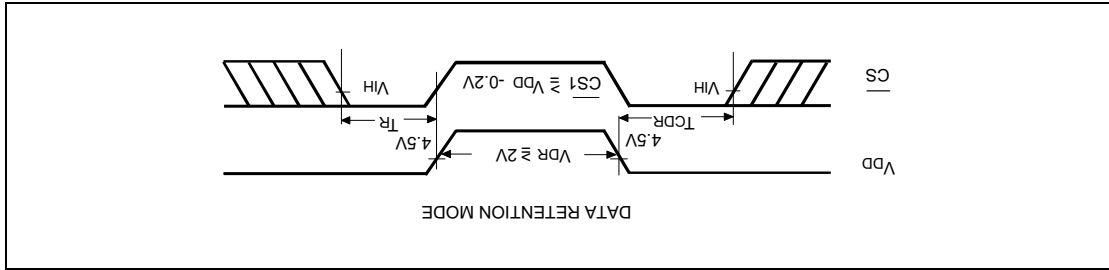
Timing Waveforms, continued



Notes:
1. Winbond reserves the right to make changes to its products without prior notice.
2. Purchasers are responsible for performing appropriate quality assurance testing on products intended for use in applications where personal injury might occur as a consequence of product failure.

PART NO.	ACCESS TIME (ns)	OPERATING CURRENT MAX. (mA)	STANDBY CURRENT MAX. (µA)	PACKAGE
W24257Q-70L	70	65	30	Standard type one TSOP
W24257Q-70LL	70	65	15	Standard type one TSOP
W24257S-70L	70	65	30	330 mil SOP
W24257S-70LL	70	65	15	330 mil SOP

ORDERING INFORMATION



DATA RETENTION WAVEFORM

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
VDD for Data Retention	VDR	$CS \geq V_{DD} - 0.2V$	2.0	-	-	V
Data Retention Current	I _{DDPR}	$CS \geq V_{DD} - 0.2V$ V _{DD} = 3V	LL	-	-	µA
Chip Deselect to Data Retention Time	T _{CDR}	See data retention waveform	L	-	-	µA
			0	-	-	ns
Operation Recovery Time	T _R	waveform	TRC*	-	-	ns

TRC* = Read Cycle Time

(T_A = 0 to 70° C)

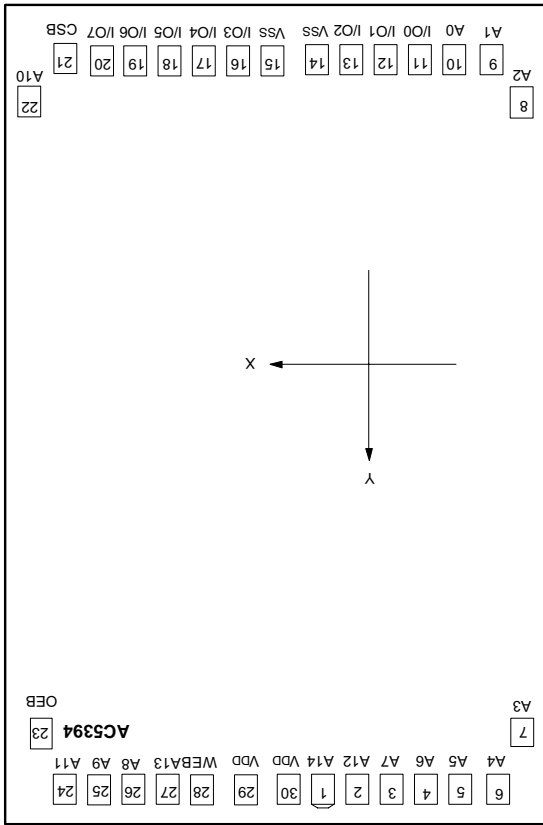
DATA RETENTION CHARACTERISTICS



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Note: For bare chip form (C.O.B.) applications, the substrate must be connected to VDD or left floating in the PCB layout.

PAD NO.	X	Y
1	-232.25	1445.22
2	-351.70	1445.22
3	-471.15	1445.22
4	-590.60	1445.22
5	-710.05	1445.22
6	-829.50	1445.22
7	-922.79	1362.24
8	-922.79	-1306.11
9	-857.86	-1452.79
10	-738.41	-1452.79
11	-594.84	-1414.13
12	-451.06	-1414.13
13	-310.67	-1414.13
14	-171.78	-1405.28
15	24.45	-1405.28
16	151.80	-1414.13
17	298.07	-1414.13
18	443.28	-1414.13
19	588.20	-1414.13
20	732.84	-1414.13
21	871.11	-1452.79
22	922.75	-1312.15
23	922.75	1373.67
24	810.09	1445.22
25	690.64	1445.22
26	571.19	1445.22
27	451.74	1445.22
28	332.29	1445.22
29	120.25	1444.65
30	-93.23	1444.65



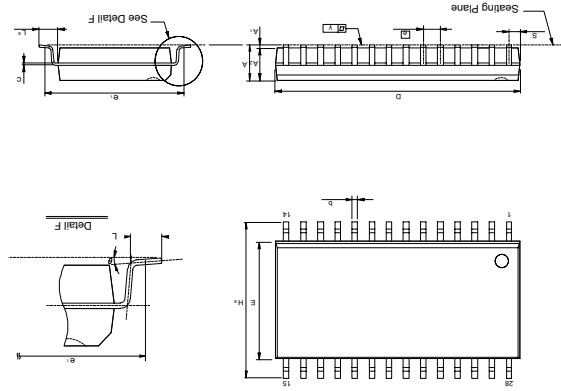
BONDING PAD DIAGRAM



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PACKAGE DIMENSIONS

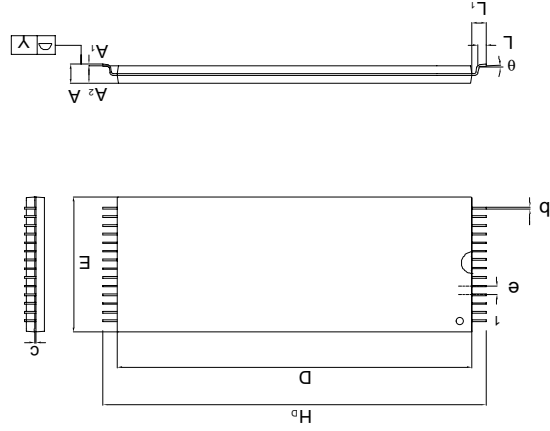
28-pin SO Wide Body



Symbol	Min.	Nom.	Max.	Dimension in mm	Dimension in Inches
A	0.004	—	0.10	—	—
A1	0.093	0.098	0.103	2.38	2.49
A2	0.014	0.016	0.020	0.36	0.41
b	0.008	0.010	0.20	0.25	0.38
c	—	0.713	0.733	18.11	18.62
D	0.326	0.331	0.396	8.28	8.41
E	0.044	0.050	0.056	1.12	1.27
H	0.453	0.465	0.477	11.51	11.81
H1	0.028	0.036	0.044	0.71	0.91
L	0.059	0.067	0.075	1.50	1.70
L1	—	0.047	—	—	1.19
S	—	—	0.004	—	0.10
Y	—	—	—	—	—
theta	0°	—	10°	0°	10°

- Notes:**
1. Dimension D Max. & S include mold flash or the burrs.
 2. Dimension b does not include dambar protrusion/intrusion.
 3. Dimension D & E include mold mismatch and determined at the mold parting line.
 4. Controlling dimension: Inches.
 5. General appearance spec should be based on final visual inspection spec.

28-pin Standard Type One TSOP



Symbol	Min.	Nom.	Max.	Dimension in mm	Dimension in Inches
A	0.047	—	0.05	1.20	—
A1	0.002	0.006	0.006	0.05	0.15
A2	0.035	0.040	0.041	0.95	1.00
b	0.007	0.008	0.011	0.17	0.20
c	0.004	0.006	0.008	0.10	0.15
D	0.461	0.465	0.469	11.70	11.80
E	0.311	0.315	0.319	7.90	8.00
H	0.520	0.528	0.536	13.20	13.40
H1	0.022	0.022	0.028	0.55	0.70
L	0.020	0.024	0.028	0.50	0.60
L1	0.010	—	—	0.25	—
Y	0.000	—	0.004	0.00	0.10
theta	0	—	—	—	—

Controlling dimension: Millimeters

Note: All data and specifications are subject to change without notice.

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VERSION	DATE	PAGE	DESCRIPTION
A14	May 2000	1, 7, 8	Delete 28-pin DIP Package
A13	Apr. 2000	7	Typo correction in Standby Current Max.: mA->µA
A12	Nov. 1999	1, 2, 7	Change the IDD, ISB, ISB1
		4, 7	Remove the W24257-10 spc.
		8	Add in Bonding Pad Diagram

VERSION HISTORY



W24257

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